

Silicon PNP Power Transistors

2SB550

DESCRIPTION

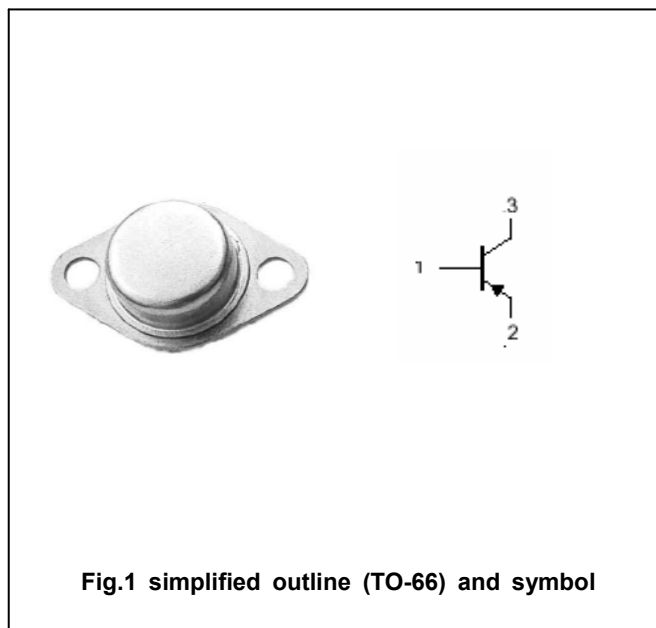
- With TO-66 package
- Low collector saturation voltage

APPLICATIONS

- For low frequency power amplification
- For low speed and power switching

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings($T_a = \square$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-100	V
V_{CEO}	Collector-emitter voltage	Open base	-70	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-5	A
P_C	Collector power dissipation	$T_C = 25 \square$	25	W
T_j	Junction temperature		150	$\square$
T_{stg}	Storage temperature		-55~150	$\square$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=-1mA; I_E=0$	-100			V
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-10mA; I_B=0$	-70			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=-1mA; I_C=0$	-5			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-5A; I_B=-0.5A$			-1.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=-5A; I_B=-0.5A$			-1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=-80V; I_E=0$			-0.1	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=-5V; I_C=0$			-0.1	mA
h_{FE}	DC current gain	$I_C=-1A; V_{CE}=-5V$	30		200	
f_T	Transition frequency	$I_C=-0.1A; V_{CE}=-10V$		5		MHz

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PACKAGE OUTLINE

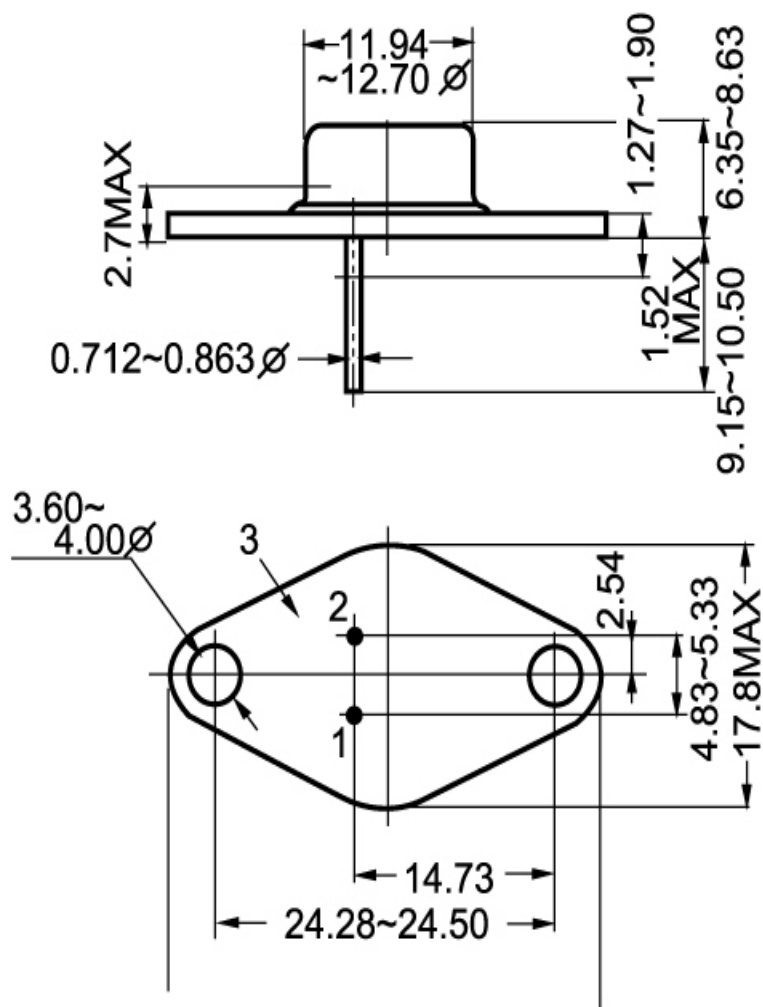


Fig.2 outline dimensions